

Design Higher Resolution Lidar Systems with New Automotive-Qualified GaN FET for Advanced Autonomy from EPC

EPC introduces the 80 V, AEC-Q101qualified EPC2252 GaN FET, for automotive-grade lidar, 48 V – 12 V DC-DC conversion, and low inductance motor drives.

EL SEGUNDO, CA, USA, January 24, 2023 /EINPresswire.com/ -- Efficient Power Conversion Corporation, the world's leader in enhancement-mode gallium nitride (eGaN®) FETs and ICs, expands the selection of automotive, off-the-shelf gallium nitride transistors with the introduction of the 80 V, 11 m Ω EPC2252 that delivers 75 A pulsed current in a 1.5 mm x 1.5 mm footprint. The EPC2252 offers power system designers significantly smaller and more efficient devices than silicon



New 80 V, 75 A Automotive-Qualified GaN FET for Higher Resolution Lidar Systems

MOSFETs for automotive-grade <u>lidar</u> found in autonomous driving and other ADAS applications, 48 V – 12 V DC-DC conversion, and low inductance motor drives.

Lower switching losses, lower conduction losses, zero reverse recovery losses, and lower drive



"The EPC2252 makes an ideal switch for automotive lidar, low inductance motors, and 48 V DC-DC conversions," Alex Lidow" EPC's co-founder and CEO

power enable high frequency designs at high efficiency. Combined with an extremely tiny footprint, these factors enable state-of-the-art power density.

The fast-switching speed of GaN, with sub-nanosecond transitions and the capability to generate high-current pulses in less than 3 ns, results in longer range and higher resolution in lidar for autonomous driving, parking, and collision avoidance.

"The EPC2252 makes an ideal switch for automotive lidar, low inductance motors, and 48 V DC-DC conversions," according to Alex Lidow, EPC's co-founder and CEO. "EPC is committed to the automotive market with a growing family of devices that enable highly efficient, low-cost vehicle electrification and autonomous driving."

Price and Availability

The EPC2252 is priced at \$0.91/ea at 1Ku and is available for immediate delivery from Digi-Key at https://www.digikey.com/en/supplier-centers/epc

Designers interested in replacing their silicon MOSFETs with a GaN solution can use the EPC <u>GaN Power Bench</u>'s cross-reference tool to find a suggested replacement based on their unique operating conditions. The cross-reference tool can be found at: https://epc-co.com/epc/DesignSupport/GaNPowerBench/CrossReferenceSearch.aspx

About EPC

EPC is the leader in enhancement mode gallium nitride (eGaN®) based power management. eGaN FETs and integrated circuits provide performance many times greater than the best silicon power MOSFETs in applications such as DC-DC converters, remote sensing technology (lidar), motor drives for eMobility, robotics, and drones, and low-cost satellites

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